

Or

- 2.** (a) A Ge transistor is used in voltage divider bias circuit has $V_{CE} = 8 \text{ V}$, $I_C = 4 \text{ mA}$, $\beta = 50$, $V_{CC} = 16 \text{ V}$, $R_C = 1.5 \text{ } \Omega$. If $S = 12$ is desired, then calculate values of R_1 , R_2 and R_E . [6]
- (b) Give comparison of CE, CB and CC amplifiers performance parameters. [6]
- 3.** (a) Define and derive the expression for f_{α} , f_{β} and f_T . [6]
- (b) Draw and explain circuit diagram of transistorized Colpitt's oscillator. Calculate the frequency of oscillations of a Colpitt's oscillator with $C_1 = C_2 = 500 \text{ pF}$ and $L = 1 \text{ mH}$. [6]

Or

- 4.** (a) The following measurements were taken while testing an amplifier using square wave input waveform : [6]
- (i) For square wave input frequency of 5 kHz the rise time of output waveform is 20 μsec ,
- (ii) For square wave input frequency of 100 Hz, there is sag of 1 V in 2.5 V amplitude observed on CRO.

Determine the bandwidth of an amplifier under test.

(b) Mention the effect of negative feedback on amplifiers performance such as : [6]

- (i) Gain
- (ii) lower cut-off frequency
- (iii) upper cut-off frequency
- (iv) Noise,
- (v) Non-linear distortion
- (vi) Frequency distortion.

5. (a) The dynamic transfer characteristic curve of transistor is :

$$i_c(\text{mA}) = 50 i_b + 1000 i_b^2.$$

Where i_b (mA) = $10 \cos 2\pi (100 t)$.

Calculate the percentage second harmonic distortion. [6]

(b) Prove that the maximum possible efficiency of a Class B amplifier is 78.5%. [7]

Or

6. (a) Explain the following parameters of Power BJT : [6]

- (i) Thermal Resistance
- (ii) Safe Operating Area.

(b) For a Class B power amplifier providing a 22 V peak signal to 8 Ω load and power supply of 25 V. Determine : [7]

(i) P_{dc}

(ii) P_{ac}

(iii) % η .

7. (a) Write a short note on : Bi-CMOS Inverter. [6]

(b) For the transistor shown in Fig. 2 has the parameter $V_T = 0.8$ V, $k = 0.5$ mA/V². Determine the values of V_{DS} and I_D . [7]

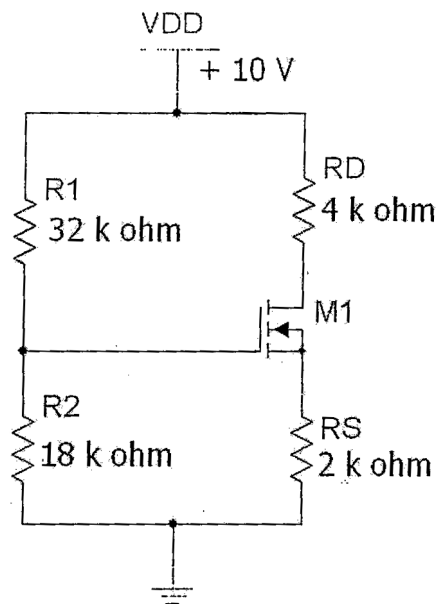


Fig. 2

Or

8. (a) The parameters of NMOSFET are $k = 0.2 \text{ mA/V}^2$, $\lambda = 0.01 \text{ V}^{-1}$, $V_T = 1.2 \text{ V}$. Calculate output resistance for : [6]

(i) $V_{GS} = 2 \text{ V}$,

(ii) $V_{GS} = 4 \text{ V}$.

(b) Explain the following non-ideal current voltage characteristics of EMOSFET : [7]

(i) Finite output resistance

(ii) Channel Length Modulation

(iii) Body Effect.